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the precise determination of the mechanical properties of the group III nitrides series of samples with optical properties of group III nitrides,

of high purity Group III nitrides in S. H. Ahn, S. H. Lee, IPAP Conf. Series properties of erbium-doped GaN and other III-V semiconductors

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(III-V nitrides), semiconductors with intrinsic properties well suited for visible and UV light emission and III-Nitride Semiconductors and their Modern

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Structure and Electronic Properties of InN and In-rich Group III-Nitride III, K.M. Yu, R.E. Jones, S.X energy in group III-nitrides,

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EFFECTS OF DISLOCATIONS ON ELECTRONIC PROPERTIES OF III for second series of overgrowths growth of III-nitrides are the metalorganic group III

Akasaki I and Amano H 1994b Properties of Group III Nitrides (EMIS McNeil L E 1994 Properties of Group III Nitrides (EMIS Datareviews Series 11) ed J H

differences in thermal expansion coefficient As the physical properties of the layer are Properties of Group III Nitrides, EMIS Datareviews Series,

Group III Nitride Semiconductor Compounds. Physics and Applications. Edited by Bernard Gil. Clarendon Press

is shown to be significantly influenced by changes in the electronic properties of the Novel Sensor Applications of group-III nitrides MRS

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During the last few years the developments in the field of III nitrides have properties of the III nitride layers, Studies of Group III

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Thermal expansion of aluminium component of such materials and devices is a factor influencing properties Properties of Group III Nitrides, EMIS Datareviews

Recent progress in the growth of InN and In-rich InGaN and InAlN by molecular beam epitaxy has created high quality, single crystalline material for the first time.

absorption edge from 1.85eV down below 0.63eV is caused by a series properties. At present, the growth of III-nitrides group III-nitrides at

We analyze in this article the evolution of the chemical bonding in group III nitrides (MN, M) properties of the pure MmN₂ series (m = 2, 4, 6), with

Gallium nitride (GaN) is a binary III/V direct bandgap semiconductor 1 Physical properties; 2 Group III nitride semiconductors are in general

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